

B2 silicide film or the like, is provided between the diffusion barrier 114a and the diffusion layer 104.

Please delete the present title, and substitute therefor the following new title:

--SEMICONDUCTOR DEVICE HAVING LAYERED INTERCONNECT
STRUCTURE WITH A COPPER OR PLATINUM CONDUCTING FILM AND A
NEIGHBORING FILM--.

IN THE CLAIMS:

Please cancel claims ~~7~~ and 8 without prejudice or disclaimer, and amend the claims remaining in the application as follows:

9. (Amended) A semiconductor device comprising a first layered interconnection structure and a second layered interconnection structure, and a plug electrically connecting said first layered interconnection structure and said second layered interconnection structure,

B3 wherein said first layered interconnection structure includes a first copper film, and a first neighboring film adjacent said first copper film and a first diffusion barrier film adjacent said first neighboring film, said first neighboring film having, as a primary constituent element thereof, an element selected from a group consisting of rhodium, ruthenium, iridium, osmium and platinum, and said first diffusion barrier film having at least one material selected from a group consisting of titanium nitride, tungsten and tantalum, and

B3 wherein said second layered interconnection structure includes a second copper film, and a second neighboring film adjacent said second copper film and a second diffusion barrier film adjacent said second neighboring film, said second neighboring film having, as a primary constituent element thereof, an element selected from a group consisting of rhodium, ruthenium iridium, osmium and platinum, and said second diffusion barrier film having at least one material selected from a group consisting of titanium nitride, tungsten and tantalum.

B4 11. (Amended) A semiconductor device according to claim 9, wherein said plug faces said first copper film, said first neighboring film and a third barrier film adjacent said plug, and at least said second neighboring film and said second diffusion barrier film are located between said second copper film and said plug.

Please add the following new claim to the application:

B5 -12. A semiconductor device according to claim 9, wherein said plug faces said first copper film, said first neighboring film, said first diffusion barrier film and a third barrier film adjacent said plug, and at least said second neighboring film and said second diffusion barrier film are located between said second copper film and said plug.
